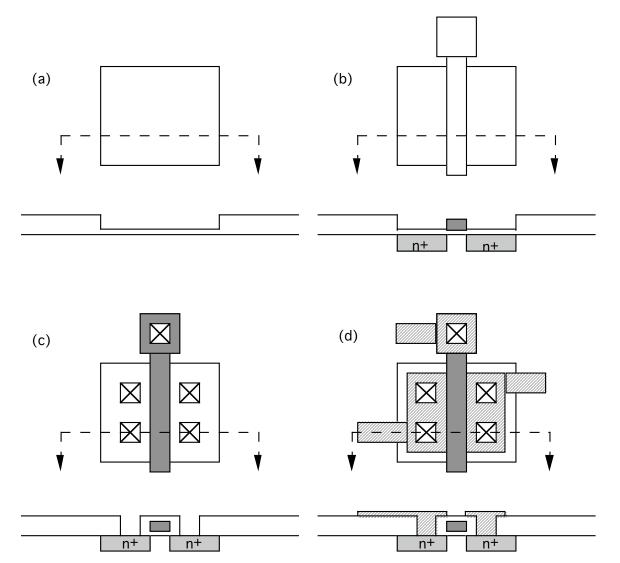
Figure 4.22 (a) Active area mask (b) Gate mask (c) Contact opening mask (d) Metal mask



Г I B I Polysilicon Below Metal Λ 2Λ T — Metal-Aluminum T Λ Interconnection⁴ I Λ 1 I I I W L Active Region-10 Λ L Γ L V ▼ L L Contact 1 1 I Polysilicon Gate Λ I n+ Oxide⁻ ^I в' Metal Oxide n+ $\begin{vmatrix} \bullet & \bullet \\ 2\Lambda & 2\Lambda & 1\Lambda & 2\Lambda \end{vmatrix}$ $H_{1\Lambda}$ n+ 12Λ

Figure 4.23 Composite top view and cross sections of a transistor with W/L = 5/1 demonstrating a basic set of ground rules.